

APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

Title of Invention	STRUCTURE AND METHOD OF FORMING BIPOLAR TRANSISTOR HAVING A SELF-ALIGNED RAISED EXTRINSIC BASE USING SELF-ALIGNED ETCH STOP LAYER
Application Type :	regular, utility
Attorney Docket Number :	FIS920030412US1
Correspondence address:	
Customer Number:	32074
	
Inventors Information:	
<u>Inventor 1:</u>	
Applicant Authority Type:	Inventor
Citizenship:	JO
Given Name:	Marwan
Middle Name:	H.
Family Name:	Khater
Residence:	
City of Residence:	Poughkeepsie
State of Residence:	NY
Country of Residence:	US
Address-1 of Mailing Address:	606 Hudson Harbour Drive
Address-2 of Mailing Address:	
City of Mailing Address:	Poughkeepsie
State of Mailing Address:	NY
Postal Code of Mailing Address:	12601
Country of Mailing Address:	US
Phone:	
Fax:	
E-mail:	
<u>Inventor 2:</u>	
Applicant Authority Type:	Inventor
Citizenship:	CA
Given Name:	Francois

Family Name:	Pagette
Residence:	
City of Residence:	Fishkill
State of Residence:	NY
Country of Residence:	US
Address-1 of Mailing Address:	1508 Max Way
Address-2 of Mailing Address:	
City of Mailing Address:	Fishkill
State of Mailing Address:	NY
Postal Code of Mailing Address:	12524
Country of Mailing Address:	US
Phone:	
Fax:	
E-mail:	

Publication Information:	
Suggested Figure for Publication - 1	
Suggested Classification -	
Suggested Technology Center -	
Total Number of Drawing Sheets - 17	

Assignee 1:	
Organization Name:	International Business Machines Corporation
Address-1 of Mailing Address:	New Orchard Road
Address-2 of Mailing Address:	
City of Mailing Address:	Armonk
State of Mailing Address:	NY
Postal Code of Mailing Address:	10504
Country of Mailing Address:	US
Phone:	
Fax:	
E-mail:	